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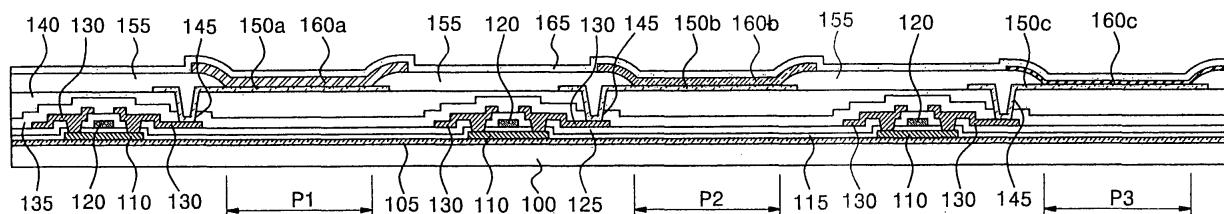
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(54) **Organic light emitting display device and method of fabricating the same**

(57) An organic light emitting display device and a method of fabricating the same. The device includes: a substrate having a first pixel region, a second pixel region and a third pixel region; a first electrode disposed on the substrate; an organic emission layer disposed on the first electrode; a second electrode disposed on the organic emission layer; and a first organic layer and a second

organic layer disposed between the first electrode and the organic emission layer. The first organic layer and the second organic layer have a combined thickness of approximately 500 to 700 Å or approximately 2000 to 2400Å in the first pixel region, approximately 1600 to 2000Å in the second pixel region, and approximately 200 to 400Å in the third pixel region.

FIG. 1C



Description**CROSS-REFERENCE TO RELATED APPLICATION****BACKGROUND OF THE INVENTION****1. Field of the Invention**

[0001] The present invention relates to a light emitting display device. More particularly, the present invention relates to an organic light emitting display device and a method of fabricating the same.

2. Description of the Related Art

[0002] The organic light emitting display device, a self-emissive display device, has an ideal structure which is thin and lightweight, made of simple components and has a simple manufacturing process. The organic light emitting display device has advantages of wide viewing angle, high picture quality, excellent display of motion pictures, high color purity, and low power consumption and low driving electric current suitable for mobile devices.

[0003] Conventional organic light emitting display devices include a substrate, a pixel electrode disposed on the substrate, an organic layer including an emission layer (EML) disposed on the pixel electrode, and a counter electrode disposed on the organic layer. The organic layer may include a hole injection layer (HIL) and a hole transport layer (HTL) disposed between the pixel electrode and the EML, and an electron transport layer (ETL) and an electron injection layer (EIL) disposed between the EML and the counter electrode.

[0004] Driving the conventional organic light emitting display device may be performed as follows. By applying electric current between the pixel electrode and the counter electrode, holes are injected from the pixel electrode into the EML via the HIL and the HTL, and electrons are injected from the counter electrode into the EML via the EIL and the ETL. The holes and electrons injected into the EML are recombined in the EML to create excitons. Light is emitted while the excitons transition from an excited state to a ground state.

[0005] In general, a conventional top emitting organic light emitting display device uses a light resonance effect so that it is important to match the thickness of the pixel electrode and the thicknesses of the HIL and HTL disposed between the EML and the pixel electrode with a possible wavelength band. The HIL enhances power consumption efficiency and the lifespan of the organic light emitting display device by facilitating the injection of holes from the pixel electrode, which is an anode. The HTL increases hole mobility and the probability of forming excitons by easily transporting holes and confining electrons to the emission region.

[0006] However, when the conventional organic layer of the organic light emitting display device is formed thinly to extend the lifespan of the device, there is a high probability of dark pixels being generated due to particles. On the other hand, when the conventional organic layer is formed thickly to reduce dark pixels, driving electric current increases while efficiency and lifespan decrease. Thus, it is difficult to form the organic layer to have an appropriate thickness.

SUMMARY

[0007] The present invention sets out to solve the above problems.

[0008] According to a first aspect of the invention, an organic light emitting display device comprises the features of Claim 1. Preferred features of this aspect of the invention are set out in Claims 2 to 7.

[0009] A second aspect of the invention provides a method of fabricating an organic light emitting display device as set out in Claim 8. Preferred features of this aspect of the invention are set out in Claims 9 to 12.

[0010] Embodiments of the invention therefore enable the combined thickness of an HIL and HTL to be individually controlled for each RGB sub-pixel, thereby reducing the number of dark pixels and increasing lifespan and efficiency.

BRIEF DESCRIPTION OF THE DRAWINGS

[0011] The above and other features of the present invention will be more readily understood by making reference to the following description of embodiments of the invention which are given by way of example. The description refers to the attached drawings, in which:

[0012] FIGs. 1A, 1B and 1C are cross-sectional views illustrating a method of fabricating an organic light emitting display device according to an embodiment of the invention;

[0013] FIGs. 2A, 2B and 2C are schematic cross-sectional views illustrating structures formed on a pixel region of each unit pixel;

[0014] FIG. 3A is a graph showing the mean number of dark pixels for each of red (R), green (G) and blue (B) sub-pixels;

[0015] FIG. 3B is a chart showing a dark pixel rate versus the combined thickness of a first organic layer and a second organic layer of a green sub-pixel;

[0016] FIGs. 4A and 4B are graphs showing a brightness ratio versus time for each of R, G and B sub-pixels, and a luminescence ratio versus time for G and B sub-pixels, respectively;

[0017] FIGs. 5A, 5B, 5C, 5D, 5E and 5F are cross-sectional views illustrating a method of forming organic layers of each sub-pixel according to an embodiment of the invention; and

[0018] FIGs. 6A, 6B, 6C, 6D and 6E are cross-sectional views illustrating a method of forming organic layers of each sub-pixel according to another embodiment of the invention.

DETAILED DESCRIPTION

[0019] The present invention will now be described more fully hereinafter with reference to the accompanying drawings, in which embodiments of the invention are shown. In the drawings, the thicknesses of layers and regions are exaggerated for clarity. The same reference numerals are used to denote the same elements.

[0020] FIGs. 1A, 1B and 1C are cross-sectional views illustrating a method of fabricating an organic light emitting display device according to an embodiment of the invention.

[0021] Referring to FIG. 1A, a buffer layer 105 is disposed on a substrate 100. In some embodiments, the substrate 100 may be a transparent insulating substrate. In various embodiments, the substrate 100 may be formed of glass or plastic. Here, the buffer layer 105 inhibits diffusion of moisture and impurities generated on the substrate 100, and facilitates smooth crystallization of a semiconductor layer by controlling heat transmission speed during crystallization.

[0022] Next, a semiconductor layer 110 is formed on the buffer layer 105. Here, the semiconductor layer 110 is formed by disposing an amorphous silicon layer on the buffer layer 105, crystallizing it, and then patterning it.

[0023] Further, a gate insulator 115 is formed on the buffer layer 105 and the semiconductor layer 110. Here, the gate insulator 115 is formed of one of a silicon oxide layer, a silicon nitride layer or a composite layer thereof, using physical vapor deposition (PVD) or chemical vapor deposition (CVD).

[0024] Subsequently, a gate electrode 120 is formed by depositing a gate electrode material on the gate insulator 115 and patterning the material. Here, when the gate electrode material is patterned, at least one element among a data line, a scan line, a common power line or a capacitor electrode may be formed concurrently in a predetermined region.

[0025] Also, an interlayer insulating layer 125 is formed over the entire surface of the substrate to protect elements such as the gate electrode 120.

[0026] In addition, after contact holes exposing predetermined regions of source/drain regions of the semiconductor layer 110 are formed by etching predetermined regions of the interlayer insulating layer 125 and the gate insulator 115, source/drain electrode material is deposited on the substrate 100 and then patterned so that source and drain electrodes 130 respectively contacting the source and drain regions of the semiconductor layer 110 are formed.

[0027] Here, when the source/drain electrode material is patterned, at least one element among a data line, a scan line, a common power line or a capacitor electrode may be formed. Here, formation of the source and drain electrodes 130 completes formation of a thin film transistor. In one embodiment, the thin film transistor includes the semiconductor layer, the gate insulator, the gate electrode and the source and drain electrodes.

[0028] In addition, at least one of a passivation layer 135 or a planarization layer 140 is formed over the substrate 100. Here, the passivation layer 135 is an insulating layer adapted to protect elements disposed below the passivation layer 135, and the planarization layer 140 is an insulating layer adapted to remove a step coverage caused by elements disposed below the planarization layer 140.

[0029] Referring to FIG. 1B, a via hole 145 is formed to expose a part of the source/drain electrode 130 by partially etching the planarization layer 140 and the passivation layer 135.

[0030] Further, first electrode material is deposited on the substrate 100 and then patterned to form a first electrode 150 coupled to the source or drain electrode 130. Here, the first electrode 150 may be formed of a transparent conductive material, for example, indium-tin oxide (ITO) or indium zinc oxide (IZO). In one embodiment, the first electrode 150 is an anode electrode. In other embodiments, the first electrode may be a cathode electrode.

[0031] Furthermore, insulating material is formed over the substrate 100 and then patterned to form a pixel defining layer 155 exposing a predetermined region of the first electrode 150. Here, the pixel defining layer 155 results in a pixel region. The pixel region is a predetermined region of the first electrode 150 that the pixel defining layer 155 exposes.

[0032] Here, referring to FIGs. 1A and 1B, the gate electrode material or the source/drain electrode material is patterned to form a scan line, a data line and a common power line. Here, one sub-pixel may be defined by forming the scan line, the data line and the common power line. A sub-pixel; the smallest unit of the organic light emitting display device, is adapted to emit red (R), green (G) or blue (B) color light. A plurality of sub-pixels are included in the organic light emitting display device.

[0033] FIG. 1C shows a unit pixel, the smallest unit of a display that is adapted to display gradation. The unit pixel includes at least three sub-pixels respectively displaying R, G and B colors.

[0034] Three pixel regions are defined by the pixel defining layers 155. The three pixel regions are a first pixel region P1, a second pixel region P2, and a third pixel region P3.

[0035] Here, the first pixel region P 1 may include an organic layer 160a including an organic EML adapted to display R disposed on a first electrode 150a. The second pixel region P2 may include an organic layer 160b including an organic EML adapted to display G disposed on a first electrode 150b. And, the third pixel region P3 may include an organic layer 160c including an organic EML adapted to display B disposed on a first electrode 150c.

[0036] Here, a second electrode 165 is formed on the first pixel region, the second pixel region and the third pixel region P1, P2, P3 that are included in one unit pixel. In one embodiment, the second electrode 165 is a cathode electrode. In other embodiments, the second electrode may be an anode electrode. The organic light emitting display device can be completed by forming a plurality of such unit pixels.

[0037] FIGs. 2A, 2B and 2C are schematic cross-sectional views illustrating structures formed in each of the pixel regions of the unit pixels. FIGs. 2A, 2B and 2C show the structures of the organic layer in the first, second and third pixel regions P1, P2, P3 in FIG. 1C.

[0038] Referring to FIGs. 2A, 2B and 2C, first organic layers 210a, 210b, 210c, second organic layers 220a, 220b, 220c, third organic layers 230a, 230b, 230c, fourth organic layers 240a, 240b, 240c and fifth organic layers 250a, 250b, 250c are sequentially stacked on the first electrodes 150a, 150b, 150c, respectively. The second electrode 165 is then formed on the fifth organic layers 250a, 250b, 250c.

[0039] Here, the first organic layers 210a, 210b, 210c may be HILs, the second organic layers 220a, 220b, 220c may be HTLs, the third organic layers 230a, 230b, 230c may be EMLs, the fourth organic layers 240a, 240b, 240c may be ETLs, and the fifth organic layers 250a, 250b, 250c may be EILs.

[0040] Here, although not shown in the schematic cross-sectional views of FIGs. 2A, 2B and 2C, hole blocking layers (HBLs) may be further formed between the third and fourth organic layers 230a, 230b, 230c and 240a, 240b, 240c, respectively.

[0041] Here, the combined thickness of the first organic layers 210a, 210b, 210c, i.e., the HILs, and the second organic layers 220a, 220b, 220c, i.e., the HTLs, may be designed to have appropriate values in the first, second and third pixel regions P1, P2, P3.

[0042] First, the luminous efficiencies may vary according to a resonance effect depending on the combined thickness of the first and second organic layers of each of the sub-pixels R, G and B. Table 1 shows a relationship between luminous efficiency (for colors R, G and B) and the combined thickness of the first and second organic layers.

Table 1

Combined thickness of first and second organic layers	R efficiency	G efficiency	B efficiency	B CIE x	B CIE y
100	1.2	1.7	0.4	0.12	0.06
200	0.8	2.21	0.51	0.13	0.07
300	1.1	2.73	0.65	0.14	0.09
400	1.16	2.3	0.69	0.14	0.12
500	2.02	1.94	0.72	0.15	0.14
600	2.56	1.43	0.78	0.15	0.15
700	1.98	1.22	0.84	0.15	0.17
800	1.23	1.1	0.9	0.16	0.19
900	1	1	1	0.16	0.2
1000	0.91	0.83	0.89	0.16	0.18
1100	0.83	1.39	0.76	0.15	0.17
1200	0.62	1.59	0.7	0.15	0.15
1300	1.01	1.86	0.62	0.14	0.1
1400	1.28	2.1	0.54	0.13	0.08
1500	1.32	2.31	0.41	0.12	0.06
1600	1.44	2.43	0.48	0.12	0.08

(continued)

Combined thickness of first and second organic layers	R efficiency	G efficiency	B efficiency	B CIE x	B CIE y
1700	1.65	2.49	0.52	0.14	0.11
1800	1.76	2.56	0.62	0.14	0.13
1900	1.79	2.43	0.76	0.15	0.16
2000	1.88	2.11	0.86	0.16	0.19
2100	2.17	1.99	0.7	0.15	0.17
2200	2.41	1.94	0.47	0.15	0.15
2300	2.26	1.73	0.32	0.14	0.13
2400	2.01	1.62	0.29	0.13	0.1
2500	1.74	1.28	0.25	0.13	0.08
2600	1.26	1.01	0.23	0.12	0.07

[0043] Referring to Table 1, for R and G, color characteristics are somewhat satisfied even if the thicknesses of the first and second organic layers are changed, so the most efficient thickness ranges, as shown in Table 1, are approximately 500-700 Å or approximately 2000-2400 Å for R and approximately 200-400 Å or approximately 1600-2000 Å for G. The most efficient thickness ranges are selected. As for B, after limiting color characteristics such that the y color coordinate is less than 0.09, the most efficient thickness ranges within the set limit are chosen, which are approximately 200 to 400 Å or approximately 1200 to 1600 Å.

[0044] Accordingly, the R sub-pixel may be formed when the first and second organic layers have a combined thickness of approximately 500 to 700 Å or approximately 2000 to 2400 Å, the G sub-pixel may be formed when the first and second organic layers have a combined thickness of approximately 200 to 400 Å or approximately 1600 to 2000 Å, and the B sub-pixel may be formed when the first and second organic layers have a combined thickness of approximately 200 to 400 Å or approximately 1200 to 1600 Å.

[0045] FIG. 3A is a graph showing the mean number of dark pixels for each of R, G and B sub-pixels. FIG. 3B is a chart showing a dark pixel rate versus the combined thickness of first and second organic layers of a G sub-pixel.

[0046] Referring to FIGs. 3A and 3B, the brightness for each color of sub-pixel is different to adjust the white balance of a unit pixel including three unified sub-pixels. For example, the brightness of G is the highest. When the white balance is adjusted by making the combined thickness of the first and second organic layers of the R, G and B sub-pixels equal, as shown in FIG. 3A, fewer dark pixels are generated in the B or R sub-pixels, whereas more dark pixels are generated in the green G sub-pixel having the highest brightness. It may be noted that, as shown in FIG. 3B, when the organic layers of the G sub-pixel satisfy resonance conditions and are formed to be fairly thick, dark pixels in the G sub-pixel are significantly reduced in number. Thus, the first and second organic layers of the G sub-pixel may be formed to be thick.

[0047] FIGs. 4A and 4B are graphs of a brightness ratio versus time for each of R, G and B sub-pixels, and a luminescence ratio versus time for G and B sub-pixels, respectively.

[0048] In FIG. 4A, the brightness ratios of R, G and B versus time are shown. In FIG. 4B, "G_thin" represents values of a luminescence ratio of G having thin first and second organic layers, "G_thick" represents values of the luminescence ratio of G having thick first and second organic layers, "B_thin" represents values of the luminescence ratio of B having thin first and second organic layers, and "B_thick" represents values of the luminescence ratio of B having thick first and second organic layers.

[0049] In one embodiment of the invention, the combined thickness of the first and second organic layers of the B sub-pixel is thin. However, referring to FIG. 4A, the B sub-pixel has the shortest lifespan, so its brightness decreases more quickly over time than other colors having different life-spans, and thereby a color shift occurs in which the blue color turns a greenish or yellowish color. In order to solve this problem, as shown in FIG. 4B, the first and second organic layers of the B sub-pixel are formed to be thin (B_thin curve), and the first and second organic layers of the G sub-pixel are formed to be thick (G_thick curve). Consequently, the lifespan of B may approach that of G.

[0050] Thus, referring back to FIGs. 2A, 2B and 2C, the first and second organic layers 210b, 220b in the second pixel region displaying green are formed to be thick to avoid a short current between the first and second electrodes, which would reduce luminous efficiency and lifespan. On the other hand, the first and second organic layers 210c and 220c in the third pixel region displaying blue are formed to be thin because lifespan and luminous efficiency decreases as the combined thickness of the layers increases.

[0051] Here, even if the first and second organic layers 210a and 220a of the organic layer in the first pixel region displaying red are formed to be thin, dark pixels may not be generated. And, even if these layers are thick, neither lifespan nor efficiency decreases. Therefore, these layers are allowed to be thin or thick.

[0052] Thus, the first and second organic layers 210a and 220a in the first pixel region P1 may be formed to a combined thickness of approximately 500 to 700 Å or approximately 2000 to 2400 Å, the first and second organic layers 210b and 220b in the second pixel region P2 may be formed to a combined thickness of approximately 1600 to 2000 Å, and the first and second organic layers 210c and 220c in the third pixel region P3 may be formed to a combined thickness of approximately 200 to 400 Å.

[0053] Here, the first pixel region P1 may include the R sub-pixel, the second region P2 may include the G sub-pixel, and the third pixel region P3 may include the B sub-pixel.

[0054] FIGs. 5A, 5B, 5C, 5D, 5E and 5F are cross-sectional views illustrating a method of forming organic layers of each sub-pixel according to an embodiment of the invention.

[0055] Referring to FIG. 5A, several element layers 310 are formed on a substrate 300. In some embodiments, the substrate 300 may be a transparent insulating substrate. Similar to the substrate 100 described with reference to FIGs. 1A and 1B, the substrate 300 may be formed of glass or plastic.

[0056] A first sub-pixel electrode 320a, a second sub-pixel electrode 320b, and a third sub-pixel electrode 320c are coupled to source/drain electrodes of the element layers 310 formed in first, second and third pixel regions P1, P2, P3, respectively. A pixel defining layer 330 is formed to expose predetermined regions of the first, second and third sub-pixel electrodes 320a, 320b, 320c.

[0057] Further, referring to FIG. 5B, a first mask 340a is disposed over the substrate 300, and first and second organic layers 350a, 350b are deposited (D1) to a combined thickness of approximately 500 to 700 Å or approximately 2000 to 2400 Å on the first sub-pixel electrode 320a in the first pixel region.

[0058] Referring to FIG. 5C, a second mask 340b is disposed over the substrate 300, and then first and second organic layers 360a, 360b are deposited (D2) to a combined thickness of approximately 1600 to 2000 Å on the second sub-pixel electrode 320b in the second pixel region P2.

[0059] Referring to FIG. 5D, a third mask 340c is disposed over the substrate 300, and then first and second organic layers 370a, 370b are deposited (D3) to a combined thickness of approximately 200 to 400 Å on the third sub-pixel electrode 320c in the third pixel region P3.

[0060] Referring to FIG. 5E, a fourth mask 340d is disposed over the substrate 300, and then the combined third, fourth and fifth organic layers 380a, 380b and 380c are sequentially deposited (D4) on each of the first sub-pixel electrode 320a, the second sub-pixel electrode 320b and the third sub-pixel electrode 320c, respectively, of the pixel regions P1, P2, P3.

[0061] Referring to FIG. 5F, a second electrode 390 is formed in the first, second and third pixel regions P1, P2, P3 to complete the formation of an organic light emitting display device in which the first and second organic layers 350a and 350b are formed to a combined thickness of approximately 500 to 700 Å or approximately 2000 to 2400 Å in the first pixel region P1, the first and second organic layers 360a and 360b are formed to a combined thickness of approximately 1600 to 2000 Å in the second pixel region P2, the first and second organic layers 370a and 370b are formed to a combined thickness of approximately 200 to 400 Å in the third pixel region P3, and the third, fourth and fifth organic layers 380a, 380b, 380c are formed to have the same thicknesses on top of the first and second organic layers across P1, P2, P3.

[0062] FIGs. 6A, 6B, 6C, 6D and 6E are cross-sectional views illustrating a method of forming organic layers of each sub-pixel according to another embodiment of the invention.

[0063] Referring to FIG. 6A, several element layers 410 are formed on a substrate 400. In some embodiments, the substrate 400 may be a transparent insulating substrate. Similar to the substrate 100 described with reference to FIGs. 1A and 1B, the substrate may be formed of glass or plastic.

[0064] A first sub-pixel electrode 420a, a second sub-pixel electrode 420b and a third sub-pixel electrode 420c are formed on element layer 410 to contact source/drain electrodes of the element layers 410.

[0065] A pixel defining layer 430 is formed to expose predetermined regions of the sub-pixel electrodes 420a, 420b, 420c.

[0066] A light-heat conversion layer 510 and a first donor film 500a, which is formed of a first donor-first organic film 520a and a first donor-second organic film 520b having a combined thickness of approximately 200 to 400 Å, are disposed on the substrate 400.

[0067] Referring to FIG. 6B, after the first donor film 500a is set over the substrate 400, a laser 530 is radiated at a predetermined distance to transfer parts of the first donor-first organic film 520a and the first donor-second organic film 520b onto the third sub-pixel electrode 420c in the third pixel region P3 to form first and second organic layers 430a and 430b in the third pixel region P3. Here, since light energy of the laser 530 is transformed into heat energy in the light-heat conversion layer 510 and parts of the first donor-first organic film 520a and first donor-second organic film 520b are separated from the first donor film 500a, the first donor-first organic film 520 and the first donor-second organic film

520b formed on the first donor film 500a are transferred onto the third sub-pixel electrode 420c.

[0068] Then, the first donor film 500a is removed from over the substrate 400.

[0069] Referring to FIG. 6C, after locating a second donor film 500b, which is composed of a second donor-first organic film 530a and a second donor-second organic film 530b, over the substrate 400, the laser 530 is radiated at a predetermined distance to form first and second organic layers 440a and 440b having a combined thickness of approximately 1600 to 2000 Å in the second pixel region P2.

[0070] Referring to FIG. 6D, after making a third donor film 500c, which is composed of a third donor-first organic film 540a and a third donor-second organic film 540b, contact the substrate 400, the laser 530 is radiated at a predetermined distance to form first and second organic layers 450a and 450b having a combined thickness of approximately 500 to 700 Å or approximately 2000 to 2400 Å in the first pixel region P1.

[0071] Referring to FIG. 6E, after locating a fourth donor film 500d formed of a fourth donor-third organic film 550a, a fourth donor-fourth organic film 550b, and a fourth donor-fifth organic film 550c over the substrate 400, the laser 530 is radiated at a predetermined distance to form third organic layers 450c, 440c and 430c, fourth organic layers 450d, 440d and 430d, and fifth organic layers 450e, 440e and 430e in the first, second and third pixel regions P1, P2, P3, respectively.

[0072] Here, the third, fourth and fifth organic layers formed in the respective pixel regions have the same thickness.

[0073] Then, a second electrode (not illustrated) is formed on the substrate 400 and an organic light emitting display device is completed.

[0074] According to the present invention, an organic light emitting display device and a method of fabricating the same are provided.

[0075] While numerous embodiments of the present invention have been described herein, it will be apparent to those of ordinary skill in the art that various modifications in form and detail can be made to the described embodiments without departing from the scope of the present invention as defined by the appended claims and their equivalents.

Claims

1. An organic light emitting display device, comprising:

a substrate having a first pixel region, a second pixel region and a third pixel region;
a plurality of first electrodes, each of the first electrodes being disposed on the first pixel region, the second pixel region or the third pixel region;
a plurality of organic emission layers, each of the organic emission layers being disposed on a corresponding one of the first electrodes;
a second electrode disposed on the organic emission layers;
a first organic layer and a second organic layer having a combined thickness of approximately 500 to 700 Å or approximately 2000 to 2400 Å and disposed in the first pixel region;
a third organic layer and a fourth organic layer having a combined thickness of approximately 1600 to 2000 Å and disposed in the second pixel region; and
a fifth organic layer and a sixth organic layer having a combined thickness of approximately 200 to 400 Å and disposed in the third pixel region.

2. An organic light emitting display device according to claim 1, wherein the first electrodes are anode electrodes, and the second electrode is a cathode electrode.

3. An organic light emitting display device according to claim 1 or 2, wherein the first, third or fifth organic layers are hole injection layers and the second, fourth or sixth organic layers are hole transport layers.

4. An organic light emitting display device according to claim 1, 2 or 3, further comprising an electron injection layer and an electron transport layer disposed between the second electrode and each of the organic emission layers.

5. An organic light emitting display device according to any preceding claim, wherein the first pixel region is adapted to display red.

6. An organic light emitting display device according to any preceding claim, wherein the second pixel region is adapted to display green.

7. An organic light emitting display device according to any preceding claim, wherein the third pixel region is adapted to display blue.

8. A method of fabricating an organic light emitting display device, the method comprising:

forming a plurality of first electrodes on a substrate;
 defining a first pixel region, a second pixel region and a third pixel region on the substrate;
 forming a first organic layer and a second organic layer, the first organic layer and the second organic layer having a combined thickness of approximately 500 to 700 Å or approximately 2000 to 2400 Å in the first pixel region, having a combined thickness of approximately 1600 to 2000 Å in the second pixel region, and having a combined thickness of approximately 200 to 400 Å in the third pixel region;
 forming an emission layer on the substrate on which the first pixel region, the second pixel region and the third pixel region are defined; and
 forming a second electrode on the emission layer.

9. A method according to claim 8, further comprising forming at least one of a hole blocking layer, an electron transport layer or an electron injection layer on the emission layer prior to forming the second electrode.

10. A method according to claim 8 or 9, wherein said forming the first organic layer and the second organic layer, comprises:

forming the first organic layer and the second organic layer in the first pixel region using a first mask;
 forming the first organic layer and the second organic layer in the second pixel region using a second mask; and
 forming the first organic layer and the second organic layer in the third pixel region using a third mask.

11. A method according to claim 10, wherein the first organic layer is a hole injection layer and the second organic layer is a hole transport layer.

12. A method according to claim 8 or 9, wherein said forming the first organic layer and the second organic layer, comprises:

disposing a first donor film having a light-heat conversion layer and a first transfer layer on the substrate;
 forming the first organic layer and the second organic layer in the third pixel region using a heat transfer method;
 disposing a second donor film having the light-heat conversion layer and a second transfer layer on the substrate;
 forming the first organic layer and the second organic layer in the second pixel region using the heat transfer method;
 disposing a third donor film having the light-heat conversion layer and a third transfer layer on the substrate; and
 forming the first organic layer and the second organic layer in the first pixel region using the heat transfer method.

13. A method according to claim 12, wherein the first organic layer is a hole injection layer and the second organic layer is a hole transport layer.

FIG. 1A

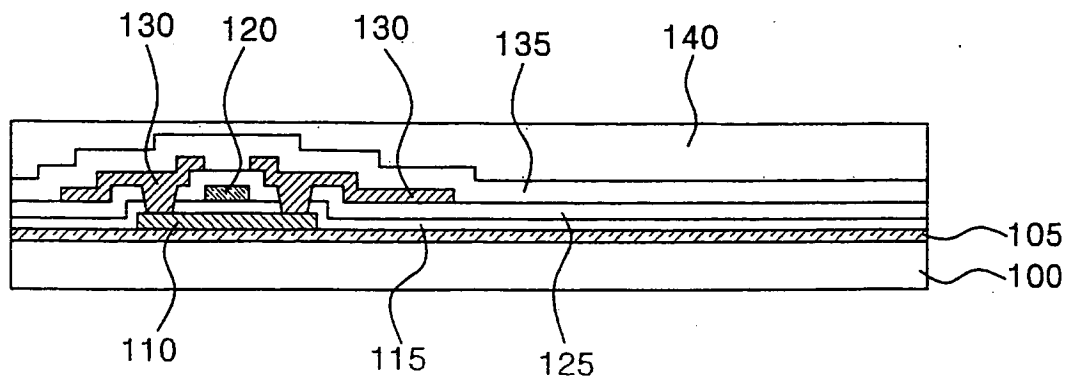


FIG. 1B

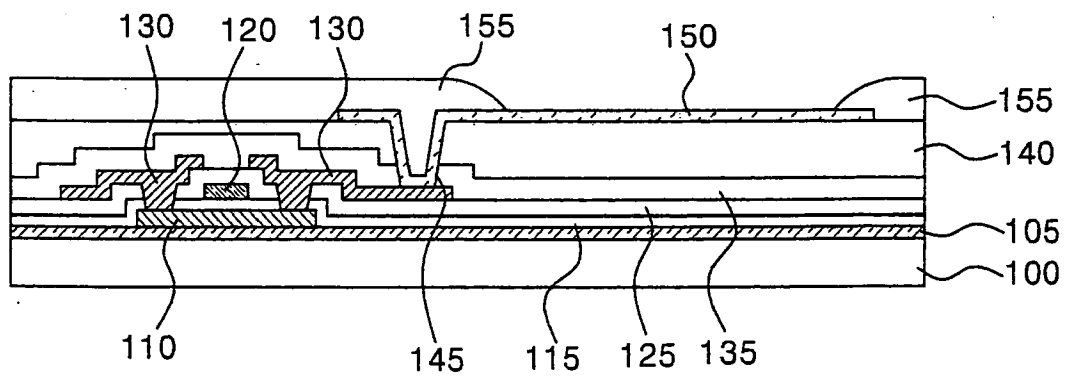


FIG. 1C

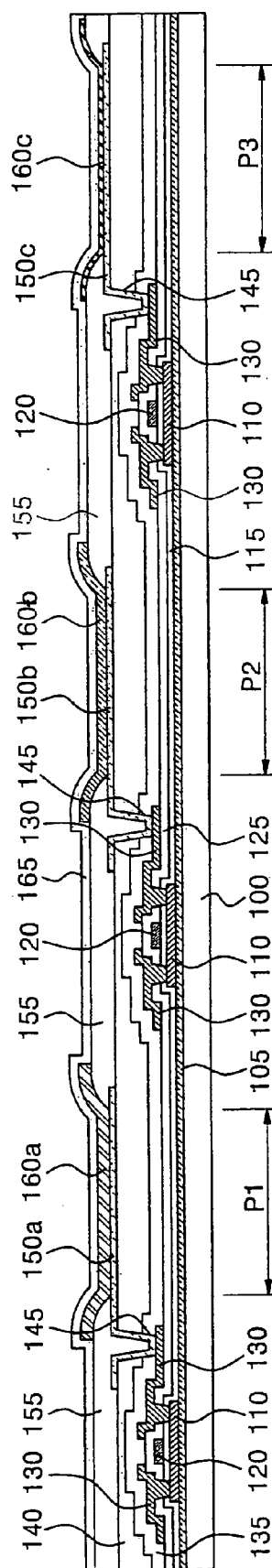


FIG. 2A

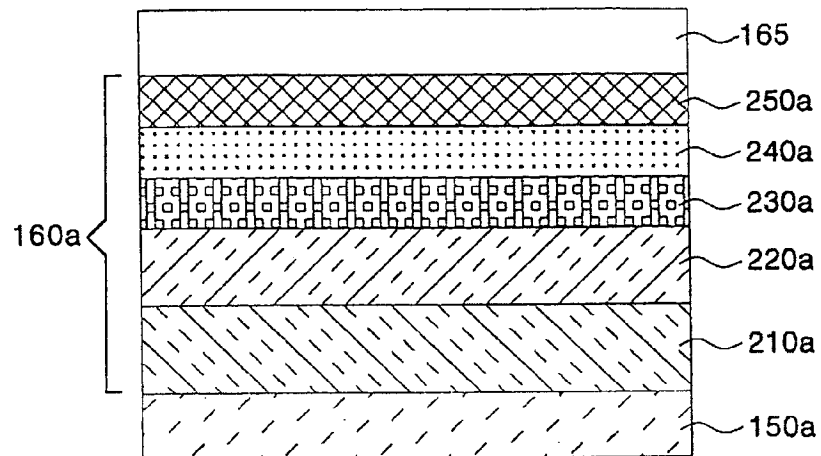


FIG. 2B

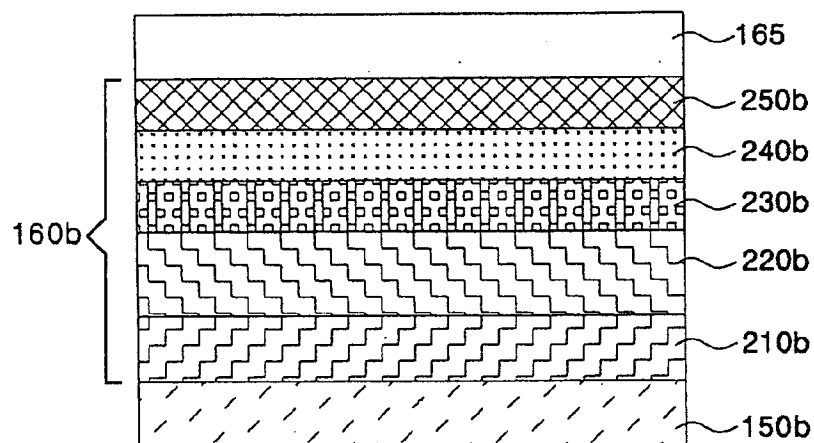


FIG. 2C

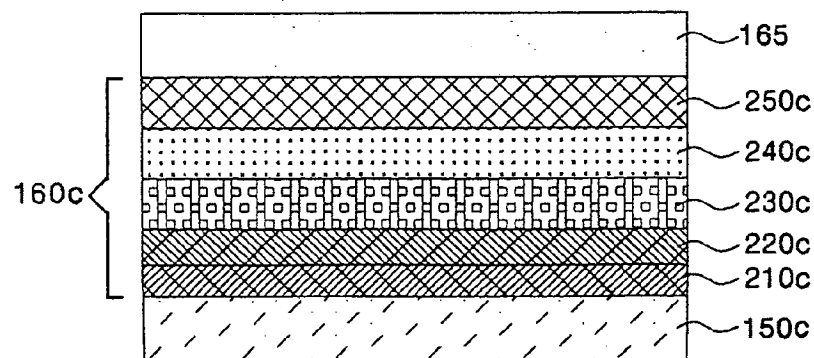


FIG. 3A

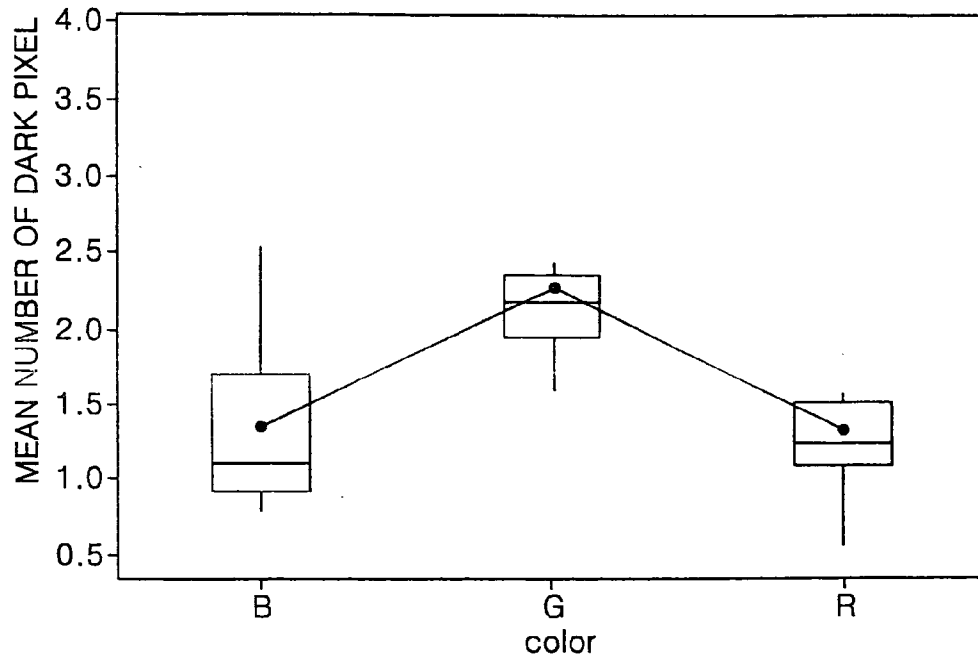


FIG. 3B

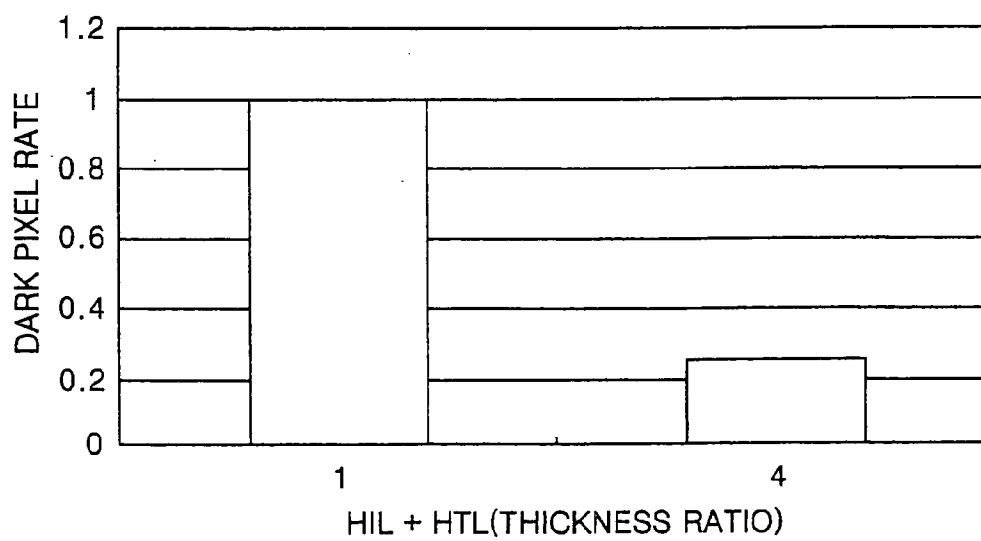


FIG. 4A

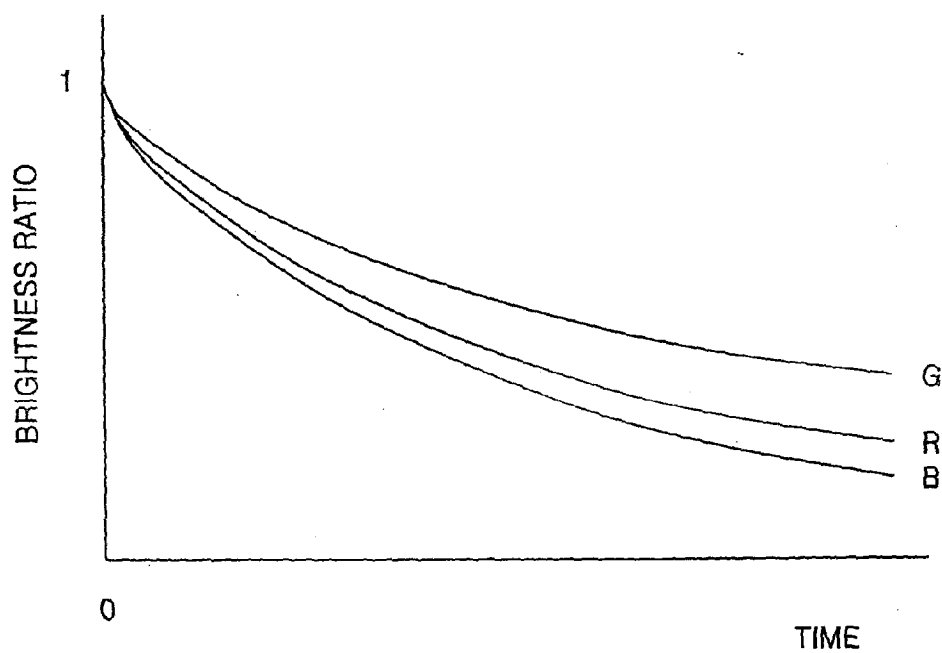


FIG. 4B

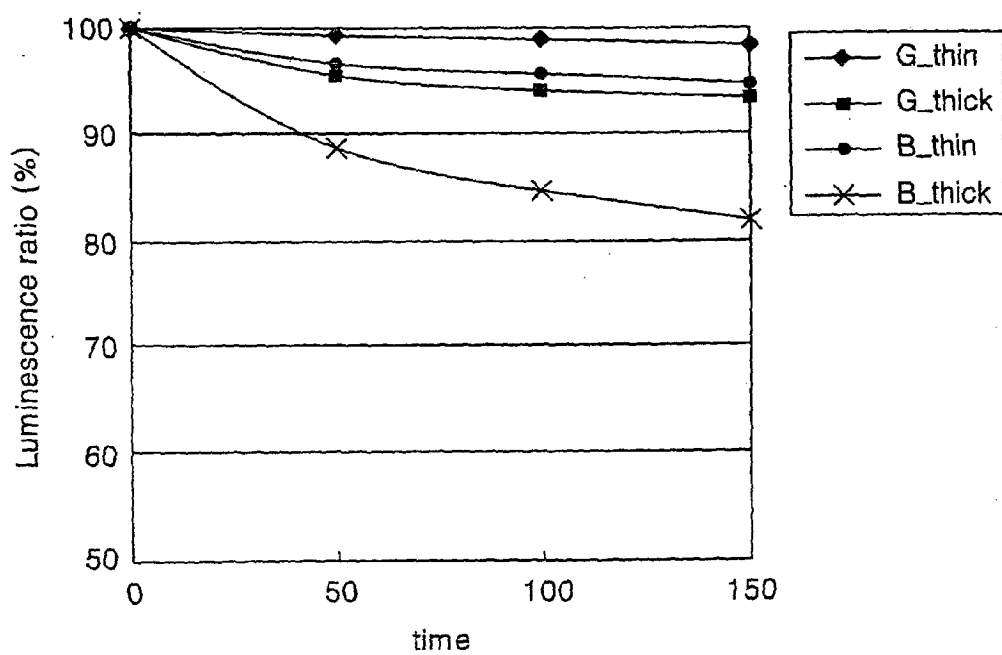


FIG. 5A

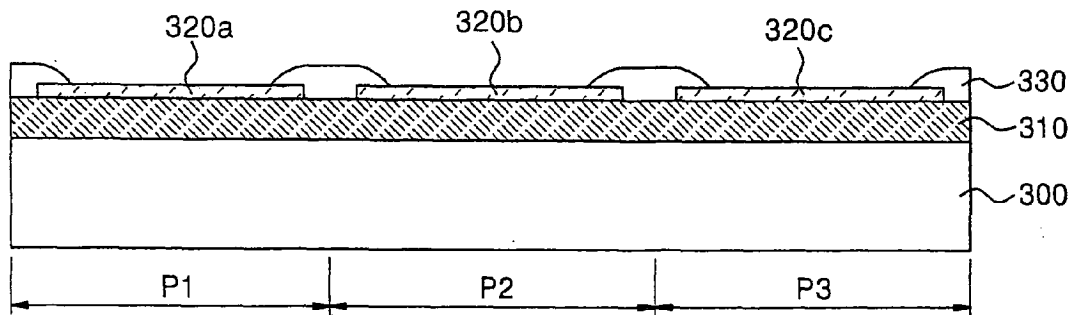


FIG. 5B

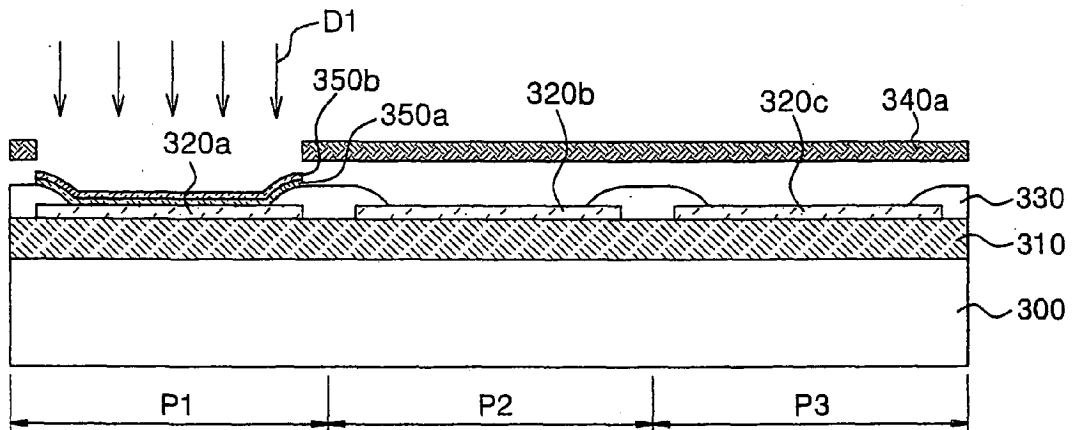


FIG. 5C

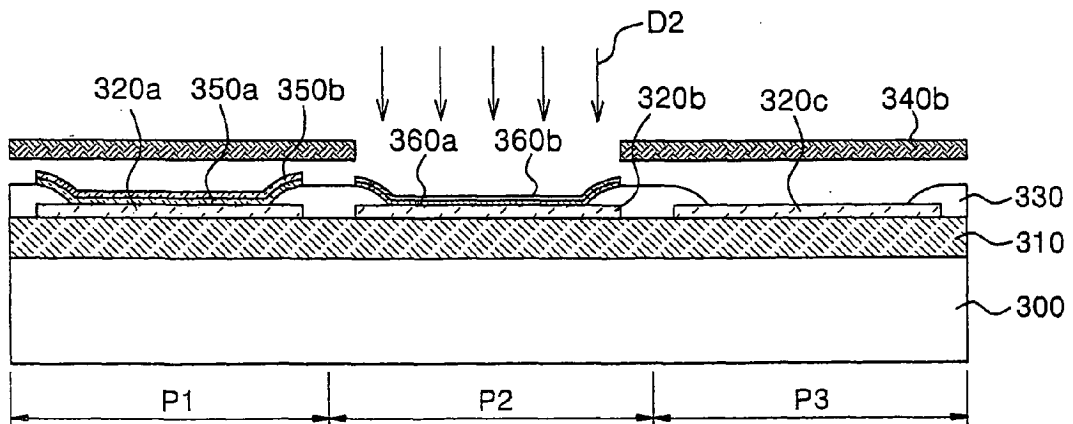


FIG. 5D

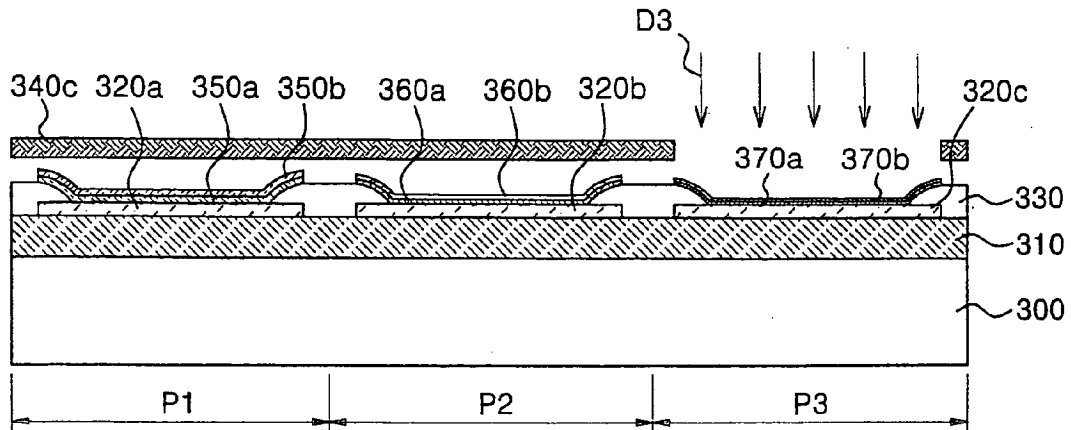


FIG. 5E

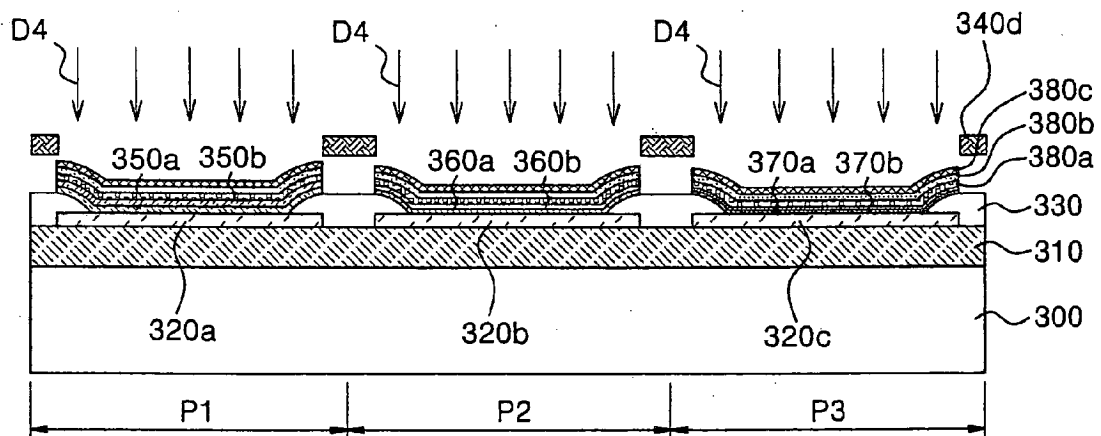


FIG. 5F

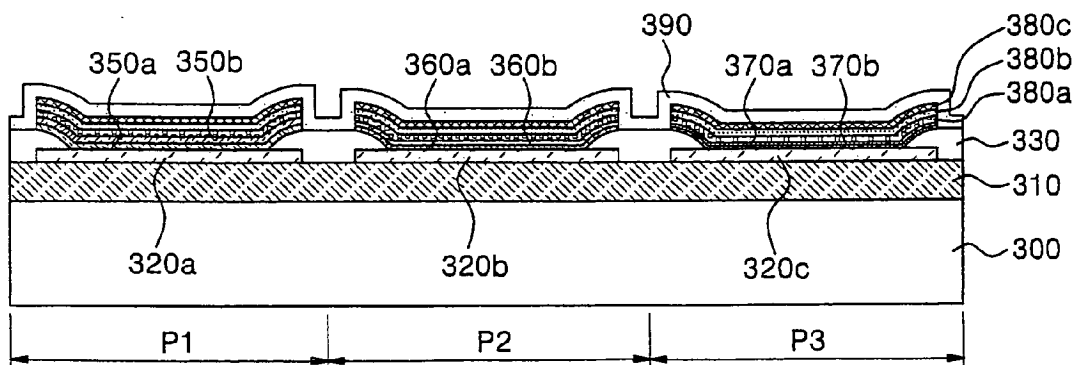


FIG. 6A

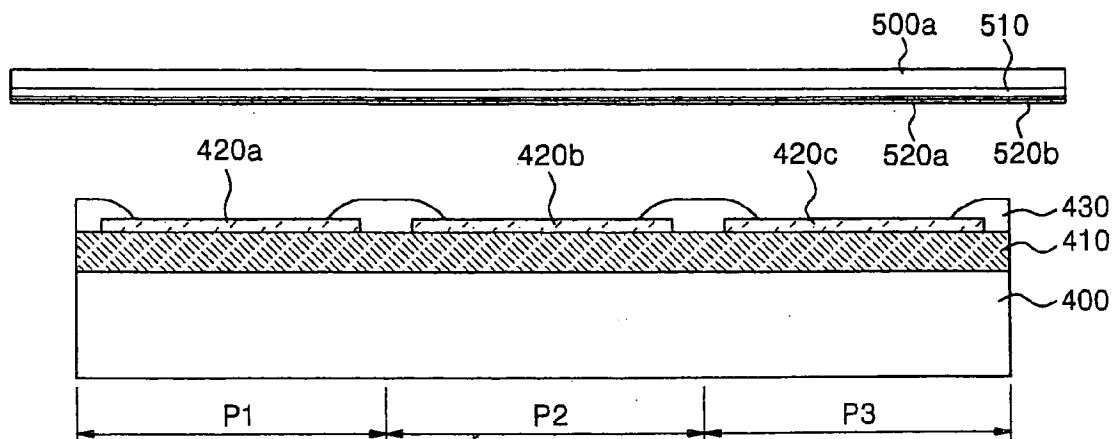


FIG. 6B

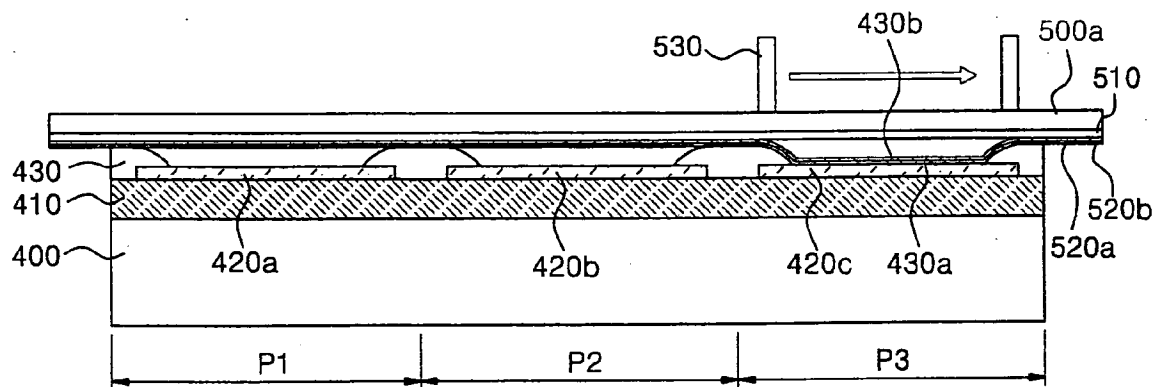


FIG. 6C

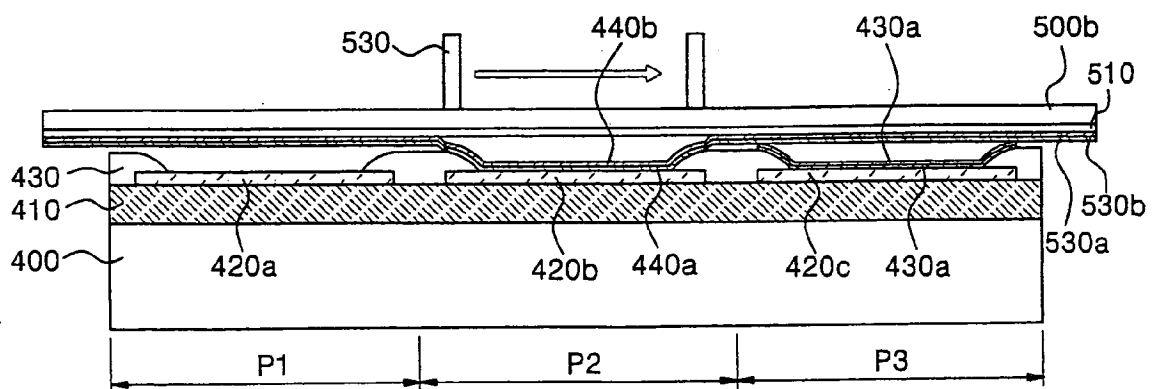


FIG. 6D

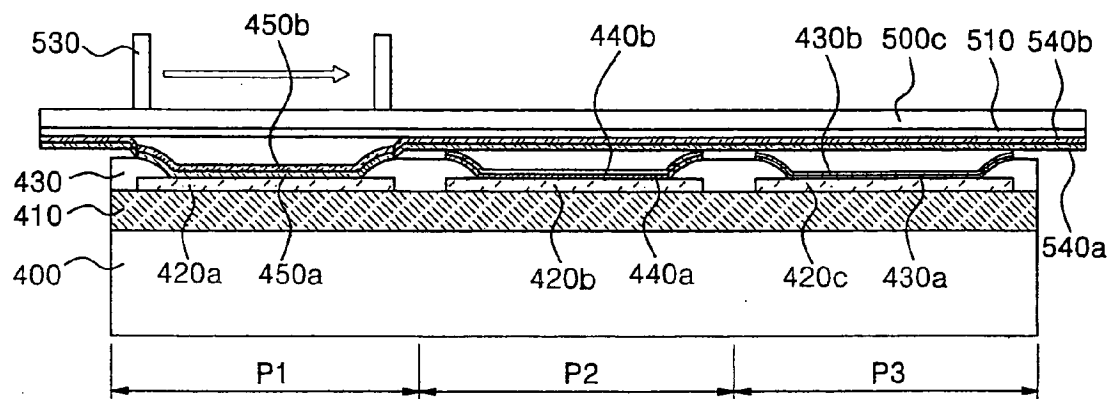
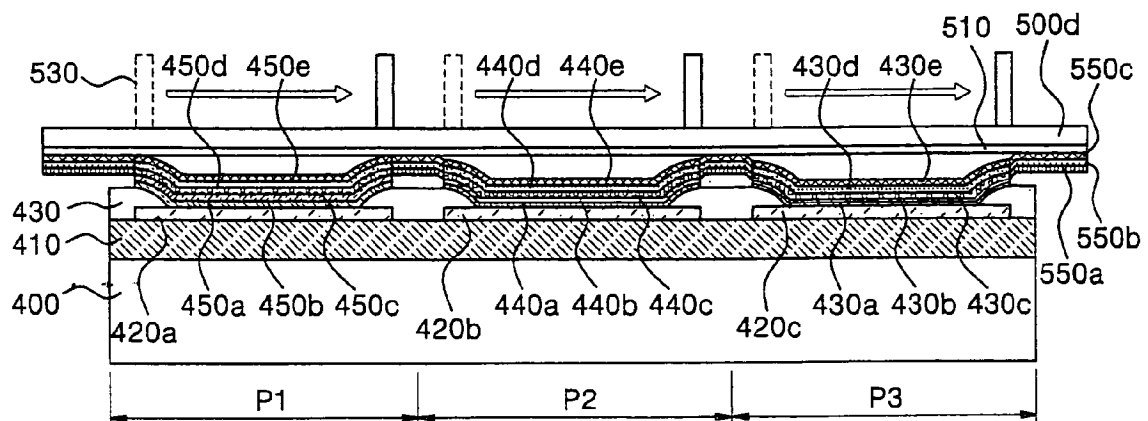


FIG. 6E



专利名称(译)	有机发光显示装置及其制造方法		
公开(公告)号	EP1777749A2	公开(公告)日	2007-04-25
申请号	EP2006255426	申请日	2006-10-23
[标]申请(专利权)人(译)	三星斯笛爱股份有限公司		
申请(专利权)人(译)	三星SDI CO. , LTD.		
当前申请(专利权)人(译)	三星DISPLAY CO. , LTD.		
[标]发明人	KIM EUN AH PARK JOON YOUNG		
发明人	KIM, EUN-AH PARK, JOON-YOUNG		
IPC分类号	H01L27/32		
CPC分类号	H01L51/5265 H01L27/3211 H01L51/5048 H01L51/5088 H01L2251/558		
优先权	1020050099836 2005-10-21 KR		
其他公开文献	EP1777749A3		
外部链接	Espacenet		

摘要(译)

有机发光显示装置及其制造方法。该器件包括：基板，具有第一像素区域，第二像素区域和第三像素区域；第一电极设置在基板上；有机发光层设置在第一电极上；第二电极设置在有机发光层上；第一有机层和第二有机层设置在第一电极和有机发光层之间。第一有机层和第二有机层在第一像素区域中具有大约500至700或大约2000至2400的组合厚度，在第二像素区域中具有大约1600至2000埃的组合厚度，并且在第三像素区域中具有大约200至400埃的组合厚度。。

FIG. 1C

